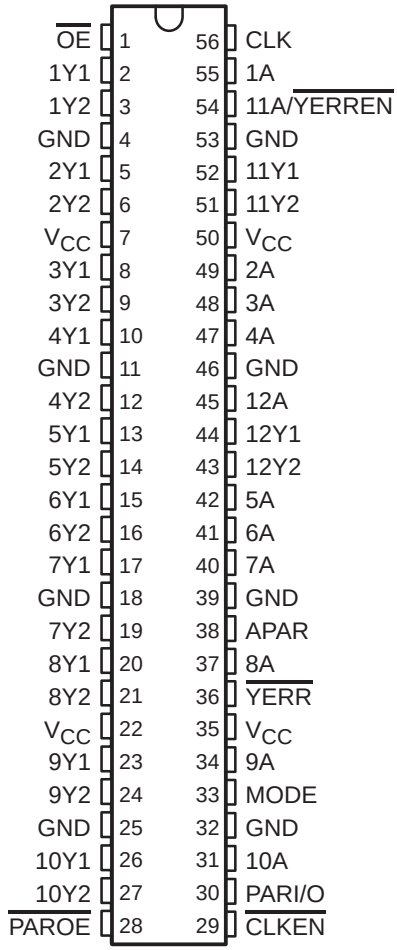
- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Checks Parity**
- **Able to Cascade With a Second SN74ALVCH16903**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL), Thin Shrink Small-Outline (DGG), and Thin Very Small-Outline (DGV) Packages**

DGG, DGV, OR DL PACKAGE
(TOP VIEW)



description

This 12-bit universal bus driver is designed for 2.3-V to 3.6-V V_{CC} operation.

The SN74ALVCH16903 has dual outputs and can operate as a buffer or an edge-triggered register. In both modes, parity is checked on APAR, which arrives one cycle after the data to which it applies. The $\overline{YERR}$ output, which is produced one cycle after APAR, is open drain.

MODE selects one of the two data paths. When MODE is low, the device operates as an edge-triggered register. On the positive transition of the clock (CLK) input and when the clock-enable ($\overline{CLKEN}$) input is low, data set up at the A inputs is stored in the internal registers. On the positive transition of CLK and when $\overline{CLKEN}$ is high, only data set up at the 9A–12A inputs is stored in their internal registers. When MODE is high, the device operates as a buffer and data at the A inputs passes directly to the outputs. 11A/$\overline{YERREN}$ serves a dual purpose; it acts as a normal data bit and also enables $\overline{YERR}$ data to be clocked into the $\overline{YERR}$ output register.

When used as a single device, parity output enable ($\overline{PAROE}$) must be tied high; when parity input/output (PARI/O) is low, even parity is selected and when PARI/O is high, odd parity is selected. When used in pairs and $\overline{PAROE}$ is low, the parity sum is output on PARI/O for cascading to the second SN74ALVCH16903. When used in pairs and $\overline{PAROE}$ is high, PARI/O accepts a partial parity sum from the first SN74ALVCH16903.

A buffered output-enable ($\overline{OE}$) input can be used to place the 24 outputs and $\overline{YERR}$ in either a normal logic state (high or low logic levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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description (continued)

$\overline{OE}$ does not affect the internal operation of the device. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16903 is characterized for operation from 0°C to 70°C.

Function Tables

FUNCTION

INPUTS					OUTPUTS	
$\overline{OE}$	MODE	$\overline{CLKEN}$	CLK	A	$1Y_n$† – $8Y_n$†	$9Y_n$† – $12Y_n$†
L	L	L	↑	H	H	H
L	L	L	↑	L	L	L
L	L	H	↑	H	Y_0	H
L	L	H	↑	L	Y_0	L
L	H	X	X	H	H	H
L	H	X	X	L	L	L
H	X	X	X	X	Z	Z

† n = 1, 2

PARITY FUNCTION

INPUTS						OUTPUT $\overline{YERR}$
$\overline{OE}$	$\overline{PAROE}$‡	11A/$\overline{YERREN}$§	PARI/O	Σ OF INPUTS 1A – 10A = H	APAR	
L	H	L	L	0, 2, 4, 6, 8, 10	L	H
L	H	L	L	1, 3, 5, 7, 9	L	L
L	H	L	L	0, 2, 4, 6, 8, 10	H	L
L	H	L	L	1, 3, 5, 7, 9	H	H
L	H	L	H	0, 2, 4, 6, 8, 10	L	L
L	H	L	H	1, 3, 5, 7, 9	L	H
L	H	L	H	0, 2, 4, 6, 8, 10	H	H
L	H	L	H	1, 3, 5, 7, 9	H	L
H	X	X	X	X	X	H
L	X	H	X	X	X	H

‡ When used as a single device, $\overline{PAROE}$ must be tied high.
§ Valid after appropriate number of clock pulses have set internal register

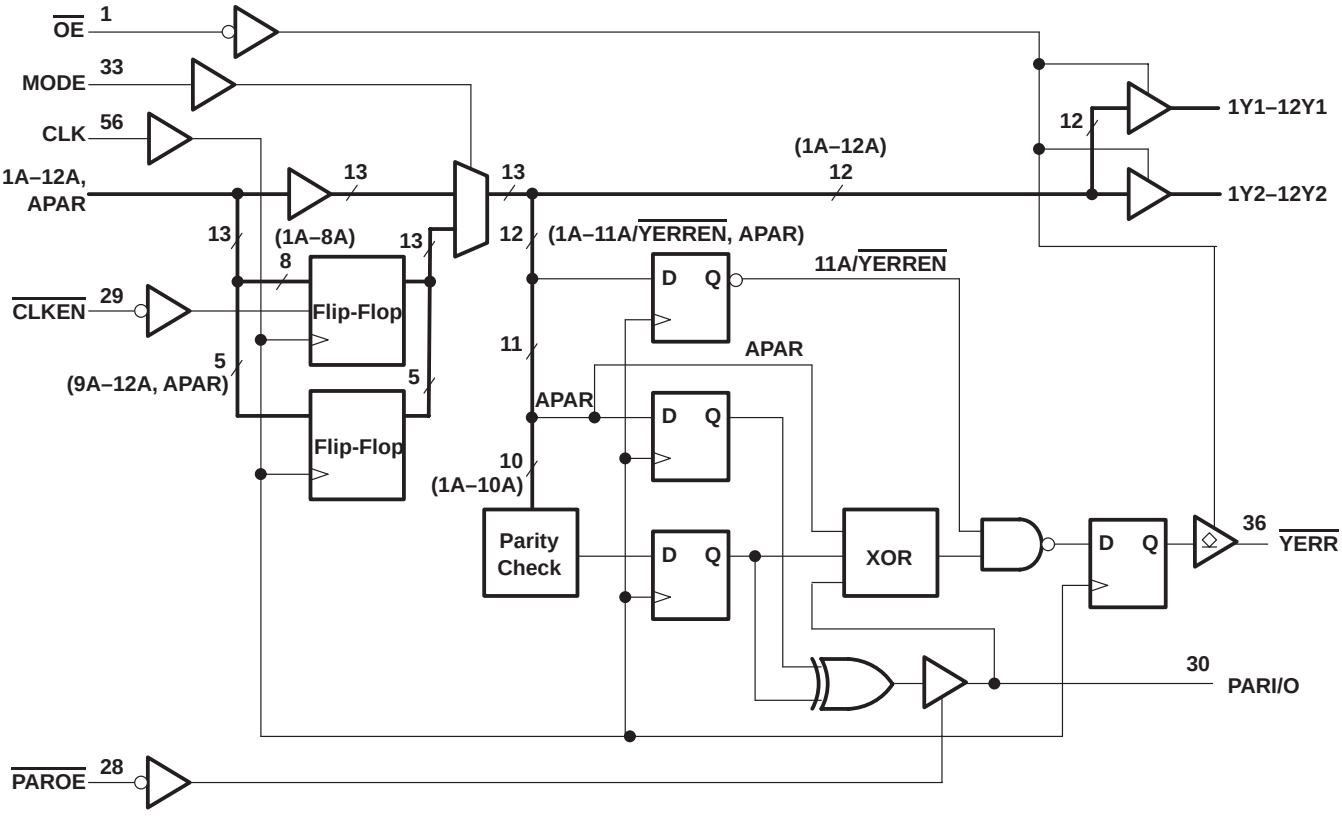
Function Tables (Continued)

PARI/O FUNCTION†

INPUTS			OUTPUT PARI/O
$\overline{\text{PAROE}}$	Σ OF INPUTS 1A – 10A = H	APAR	
L	0, 2, 4, 6, 8, 10	L	L
L	1, 3, 5, 7, 9	L	H
L	0, 2, 4, 6, 8, 10	H	H
L	1, 3, 5, 7, 9	H	L
H	X	X	Z

† This table applies to the first device of a cascaded pair of ALVCH16903 devices.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 4.6 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Continuous output current, I_O . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DGV package . . . . . 86°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

				MIN	MAX	UNIT
V_{CC}	Supply voltage			2.3	3.6	V
V_{IH}	High-level input voltage	V_{CC} = 2.3 V to 2.7 V		1.7		V
		V_{CC} = 2.7 V to 3.6 V		2		
V_{IL}	Low-level input voltage	V_{CC} = 2.3 V to 2.7 V			0.7	V
		V_{CC} = 2.7 V to 3.6 V			0.8	
V_I	Input voltage			0	V_{CC}	V
V_O	Output voltage			0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 2.3 V	Y port		–12	mA
		V_{CC} = 2.7 V			–12	
		V_{CC} = 3 V	PARI/O		–12	
			Y port		–24	
I_{OL}	Low-level output current	V_{CC} = 2.3 V	Y port		12	mA
		V_{CC} = 2.7 V			12	
		V_{CC} = 3 V	PARI/O		12	
			Y port		24	
			$\overline{YERR}$ output		24	
$\Delta t/\Delta v$	Input transition rise or fall rate			0	10	ns/V
T_A	Operating free-air temperature			0	70	°C

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}	Y port	I_{OH} = –100 μA		2.3 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –6 mA,	V_{IH} = 1.7 V	2.3 V	2			
		I_{OH} = –12 mA	V_{IH} = 1.7 V	2.3 V	1.7			
			V_{IH} = 2 V	2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA,	V_{IH} = 2 V	3 V	2			
	PARI/O	I_{OH} = –12 mA,	V_{IH} = 2 V	3 V	2			
V_{OL}	Y port	I_{OL} = 100 μA		2.3 V to 3.6 V			0.2	V
		I_{OL} = 6 mA,	V_{IL} = 0.7 V	2.3 V			0.4	
		I_{OL} = 12 mA	V_{IL} = 0.7 V	2.3 V			0.7	
			V_{IL} = 0.8 V	2.7 V			0.4	
		I_{OL} = 24 mA,	V_{IL} = 0.8 V	3 V			0.55	
	PARI/O	I_{OL} = 12 mA,	V_{IL} = 0.8 V	3 V			0.55	
	$\overline{YERR}$ output	I_{OL} = 24 mA		3 V			0.5	
I_I		V_I = V_{CC} or GND		3.6 V			±5	μA
$I_{I(hold)}$		V_I = 0.7 V		2.3 V	45			μA
		V_I = 1.7 V		2.3 V	–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V		3 V	–75			
		V_I = 0 to 3.6 V‡		3.6 V			±500	
I_{OH}	$\overline{YERR}$ output	V_O = V_{CC}		0 to 3.6 V			±10	μA
I_{OZ}§		V_O = V_{CC} or GND		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND,	I_O = 0	3.6 V			40	μA
ΔI_{CC}		One input at V_{CC} –0.6 V,	Other inputs at V_{CC} or GND	3 V to 3.6 V			750	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5.5		pF
	Data inputs					5.5		
C_o	$\overline{YERR}$ output	V_O = V_{CC} or GND		3.3 V		5		pF
	Data outputs					6		
C_{io}	PARI/O	V_O = V_{CC} or GND		3.3 V		7		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
§ For I/O ports, the parameter I_{OZ} includes the input leakage current.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figures 1 and 4)

				V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency				125		125		125	MHz
t_w	Pulse duration, CLK↑			3		3		3		ns
t_{su}	Setup time	1A–12A before CLK↑	Register mode	1.7		1.9		1.45		ns
		1A–10A before CLK↑	Buffer mode	5.9		5.2		4.4		
		APAR before CLK↑	Register mode	1.2		1.5		1.3		
			Buffer mode	4.6		3.6		3.1		
		PARI/O before CLK↑	Both modes	2.4		2		1.7		
		11A/$\overline{\text{YERREN}}$ before CLK↑	Buffer mode	2		1.9		1.6		
		$\overline{\text{CLKEN}}$ before CLK↑	Register mode	2.5		2.6		2.2		
t_h	Hold time	1A–12A after CLK↑	Register mode	0.4		0.25		0.55		ns
		1A–10A after CLK↑	Buffer mode	0.25		0.25		0.25		
		APAR after CLK↑	Register mode	0.7		0.4		0.7		
			Buffer mode	0.25		0.25		0.25		
		PARI/O after CLK↑	Register mode	0.25		0.25		0.4		
			Buffer mode	0.25		0.25		0.5		
		11A/$\overline{\text{YERREN}}$ after CLK↑	Buffer mode	0.25		0.25		0.4		
		$\overline{\text{CLKEN}}$ after CLK↑	Register mode	0.25		0.5		0.4		

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 4)

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}				125		125		125		MHz
t_{pd}	Buffer mode	A	Y	1	4.4		4.2	1.1	3.8	ns
	Both modes	CLK	$\overline{\text{YERR}}$	1	5.7		4.9	1.4	4.4	
			PARI/O	1.2	8.6		7.9	1.7	6.6	
t_{pd}†	Both modes	CLK	PARI/O	1	6.8		5.2	1.3	4.5	ns
t_{pd}	Both modes	MODE	Y	1	5.9		5.8	1.3	4.9	ns
t_{PLH}	Register mode	CLK	Y	1	6.1		5.5	1.2	4.8	ns
t_{PHL}				1	5.9		4.9	1.2	4.6	
t_{en}	Both modes	$\overline{\text{OE}}$	Y	1.1	6.5		6.4	1.4	5.4	ns
		$\overline{\text{PAROE}}$	PARI/O	1	5.6		6	1	4.8	
t_{dis}	Both modes	$\overline{\text{OE}}$	Y	1	6.4		5.2	1.7	5	ns
		$\overline{\text{PAROE}}$	PARI/O	1	3.2		3.8	1.2	3.8	
t_{PLH}	Both modes	$\overline{\text{OE}}$	$\overline{\text{YERR}}$	1	3.6		4.2	1.9	4	ns
t_{PHL}				1.2	5.1		4.9	1.5	4.2	

† See Figures 2 and 5 for the load specification.

simultaneous switching characteristics (see Figures 3 and 6)†

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	Register mode	CLK	Y	1.8	6.5		6.1	1.8	5	ns
t_{PHL}				1.4	5.9		5.1	1.7	4.5	

† All outputs switching

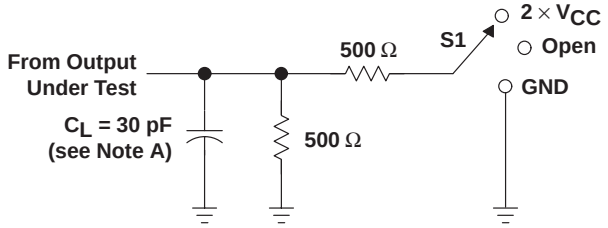
operating characteristics for buffer mode, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	57.5	65	pF
		Outputs disabled		15	17.5	

operating characteristics for register mode, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	
C_{pd}	Power dissipation capacitance	Outputs enabled	C_L = 0, f = 10 MHz	57	87.5	pF
		Outputs disabled		16.5	34	

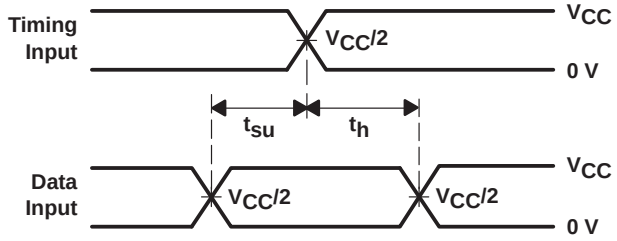
PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V



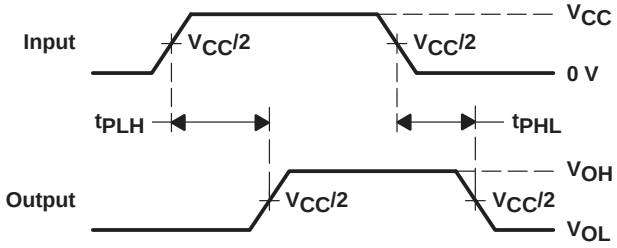
LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND

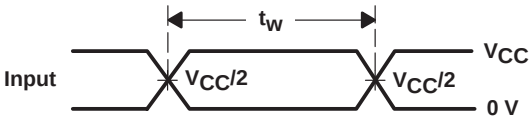
$\overline{YERR}$	S1
t_{PHL} (see Note H)	2 × V_{CC}
t_{PLH} (see Note I)	2 × V_{CC}



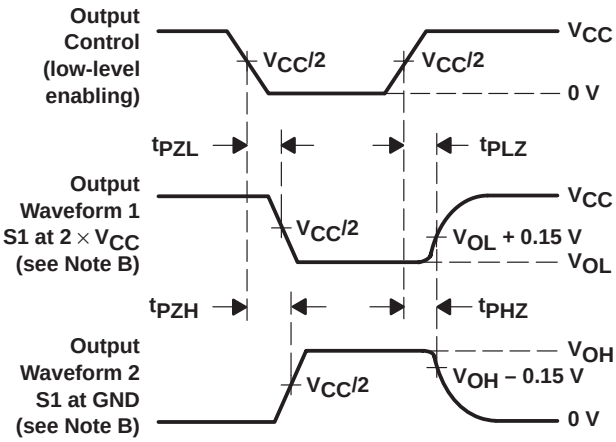
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

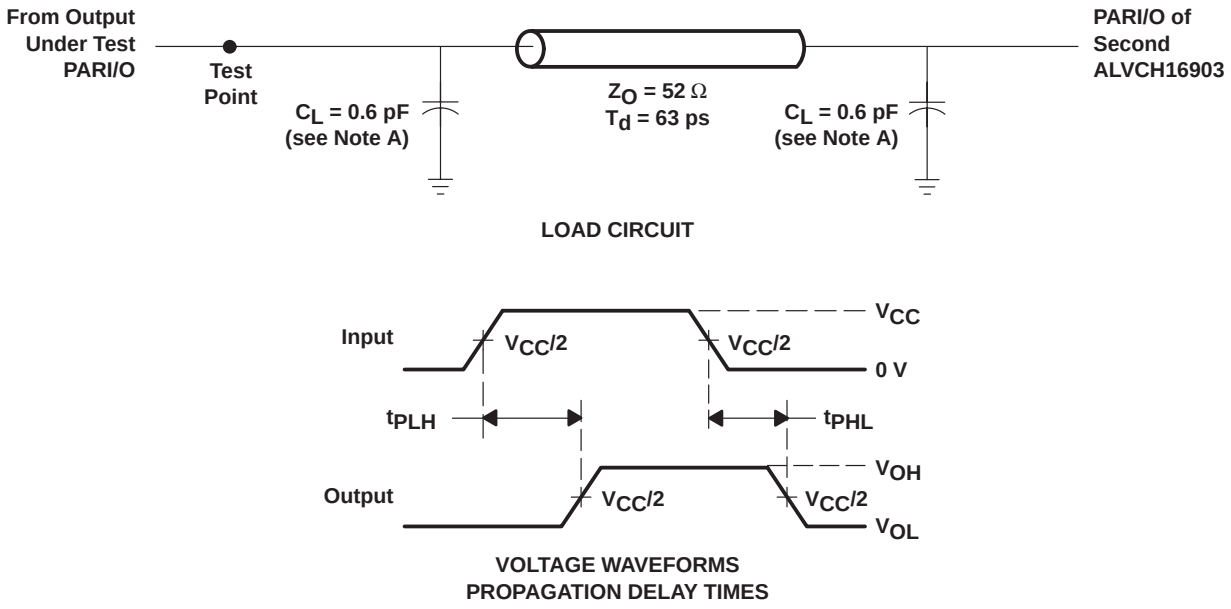


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. t_{PHL} is measured at $V_{CC}/2$.
I. t_{PLH} is measured at V_{OL} + 0.15 V.

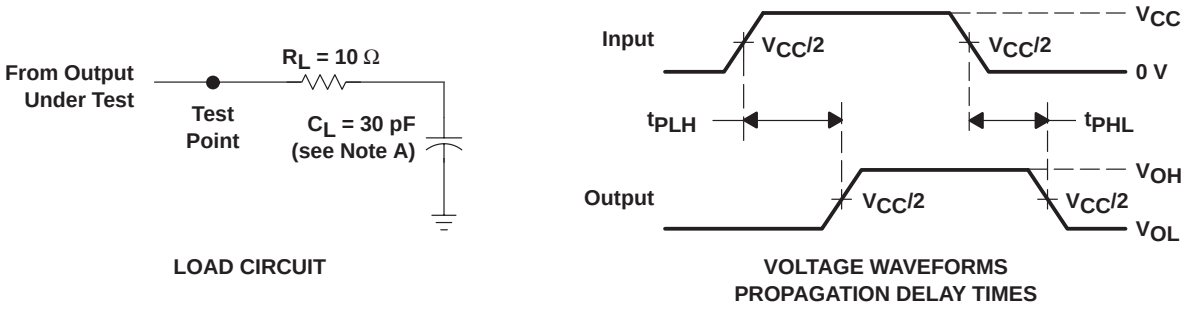
Figure 1. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V



NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
C. t_{PLH} and t_{PHL} are the same as t_{pd}.

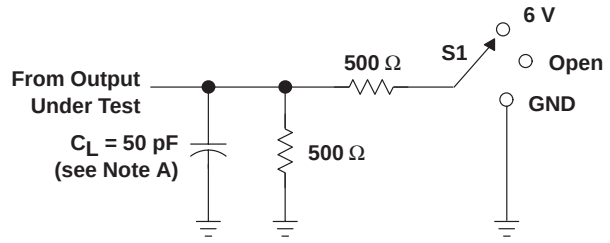
Figure 2. Load Circuit and Voltage Waveforms



NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.

Figure 3. Load Circuit and Voltage Waveforms

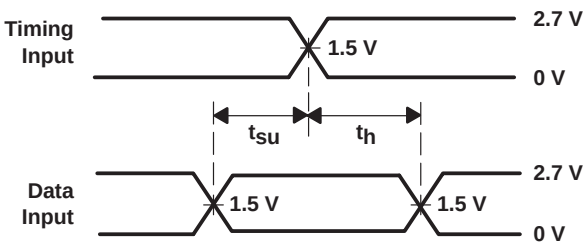
PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V



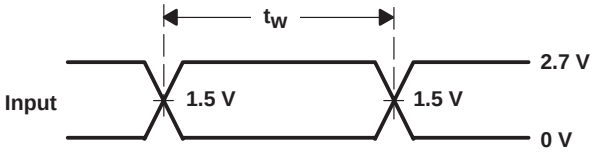
LOAD CIRCUIT

TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

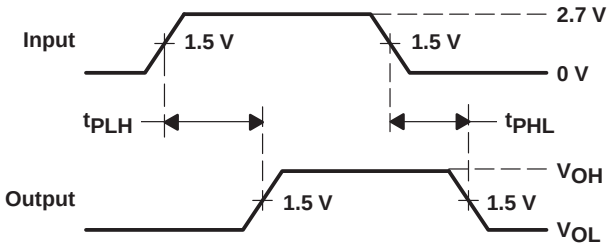
$\overline{YERR}$	S1
t_{PHL} (see Note H)	6 V
t_{PLH} (see Note I)	6 V



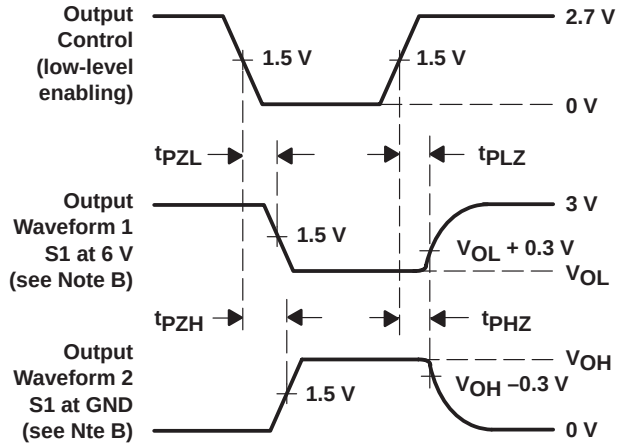
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

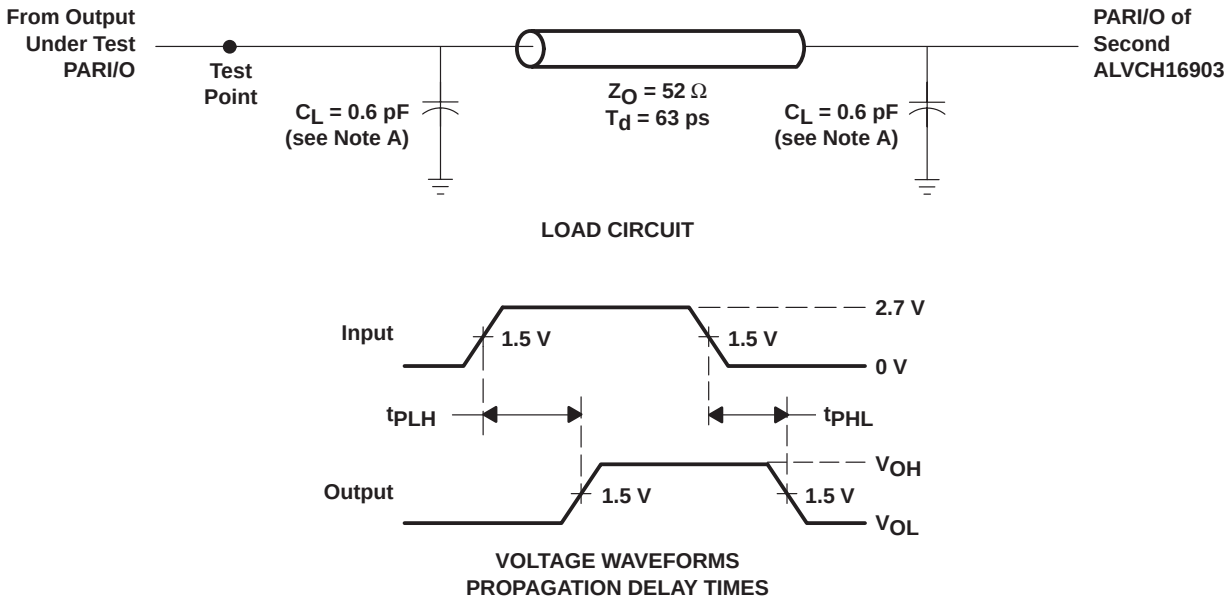


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES:
A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. t_{PHL} is measured at 1.5 V.
I. t_{PLH} is measured at V_{OL} + 0.3 V.

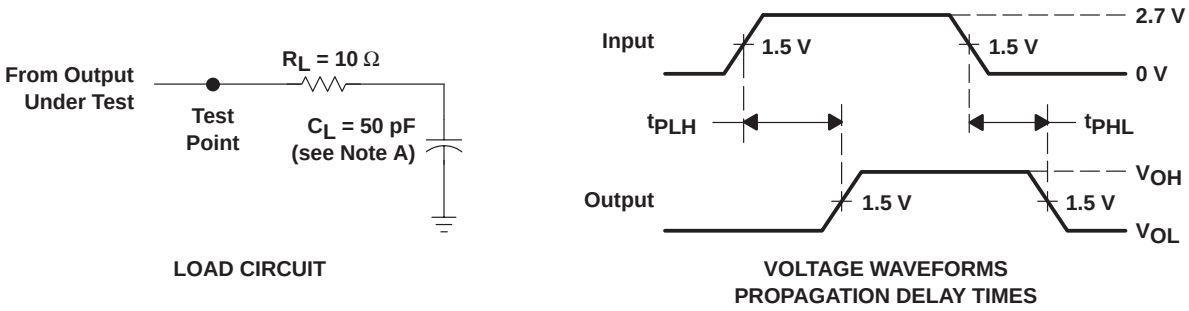
Figure 4. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V



NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
C. t_{PLH} and t_{PHL} are the same as t_{pd}.

Figure 5. Load Circuit and Voltage Waveforms



NOTES: A. C_L includes probe and jig capacitance.
B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.

Figure 6. Load Circuit and Voltage Waveforms

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